



TO-92 Plastic-Encapsulate Transistors

M8550

TRANSISTOR (PNP)

FEATURES

Power dissipation

 $P_{CM} : 0.625 \text{ W (} T_{amb}=25 \text{)}$

Collector current

 $I_{CM} : -1 \text{ A}$

Collector-base voltage

 $V_{(BR)CBO} : -40 \text{ V}$

Operating and storage junction temperature range

 $T_J, T_{stg} : -55 \text{ to } +150$ **TO—92**

1.EMITTER

2. BASE

3. COLLECTOR



1 2 3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C = -0.1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -5mA$	45		
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -100mA$	85	300	
	$h_{FE(3)}$	$V_{CE} = -1V, I_C = -800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$ $f = 30MHz$	150		MHz

* Pulse Test : pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.